



# LDPC Code Rate Adaptation Methods for NAND Flash

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The logo for Flash Memory Summit 2016, featuring a yellow sunburst icon above the text "Flash Memory" in black and "SUMMIT" in white on a blue rectangular background.

# Flash Memory Summit **Outline**

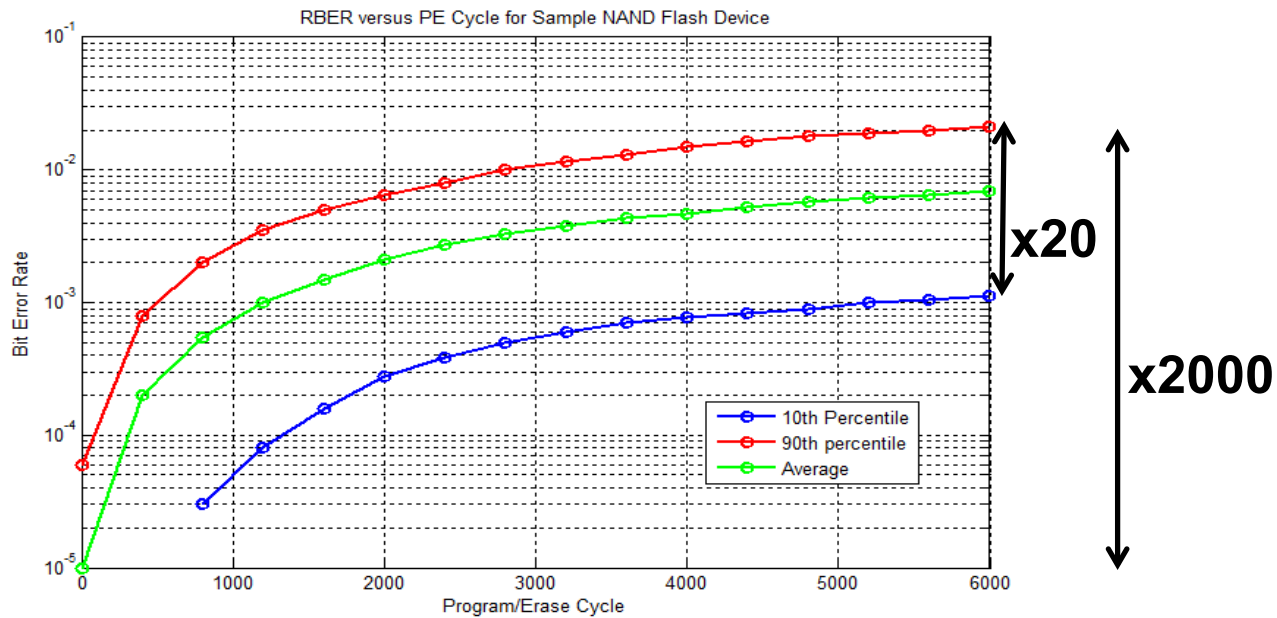
- NAND Flash Challenges
- Code Rate Selection Methods
  - Puncturing
  - Shortening
  - Custom code rates
- Performance Comparison
- Summary



# NAND Flash Challenges

- Raw BER Factors
  - NAND type (QLC,TLC,MLC,SLC)
  - Vendor selection, spare size
  - Page-to-Page variations
  - PE cycle
  - Retention time
  - Product type (Enterprise or Commercial)
  - Future NAND technology disruptions
- Multiple BER regimes within a single Controller

# Page-to-Page Variation



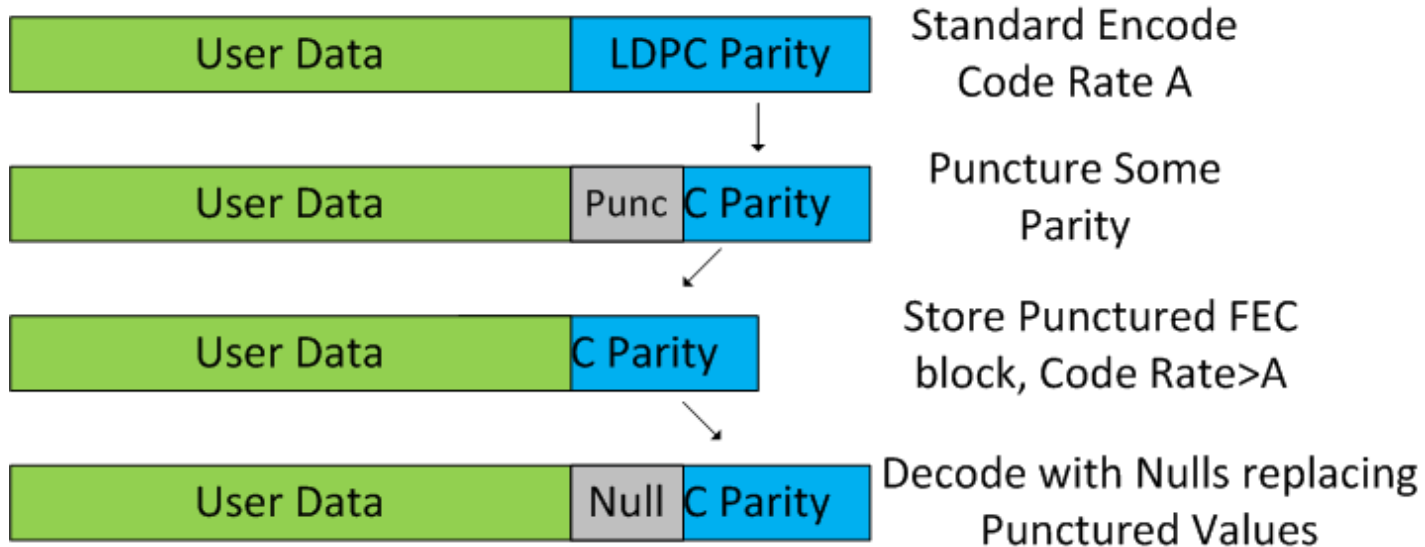
RBBER of pages at same PE cycle - 20x difference  
 RBBER over life-time - up to 2000x difference



## Code Rate Selection

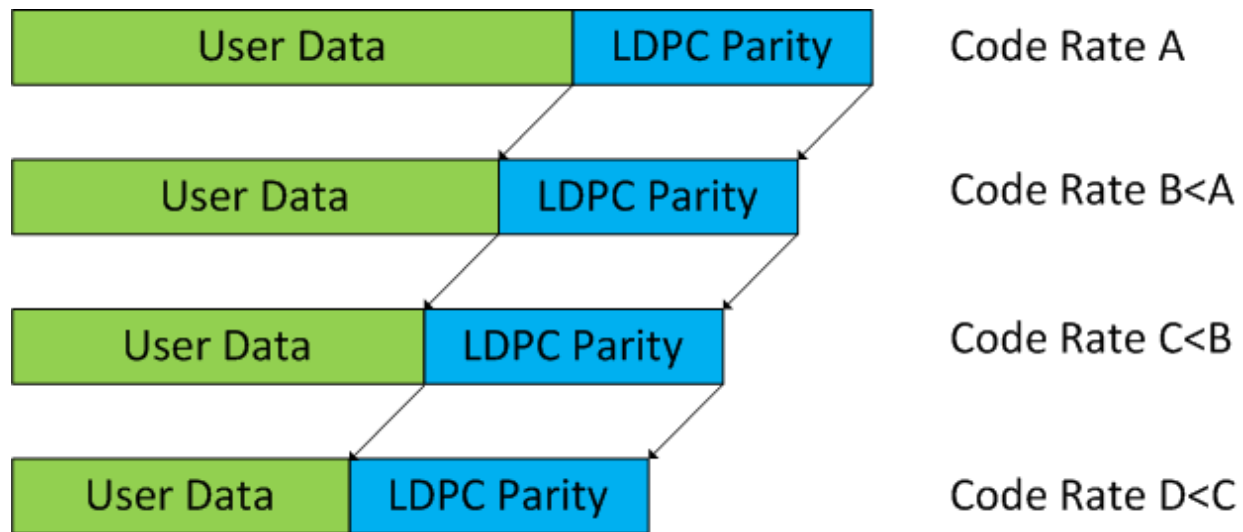
- Single low code rate protects all pages
  - Used parity is too large
  - Drive size is smaller, write-amplification is higher
- Single high code rate reduces parity overhead
  - Many pages fail as device ages
- **Multiple code rate ECC solution required**

# Puncturing



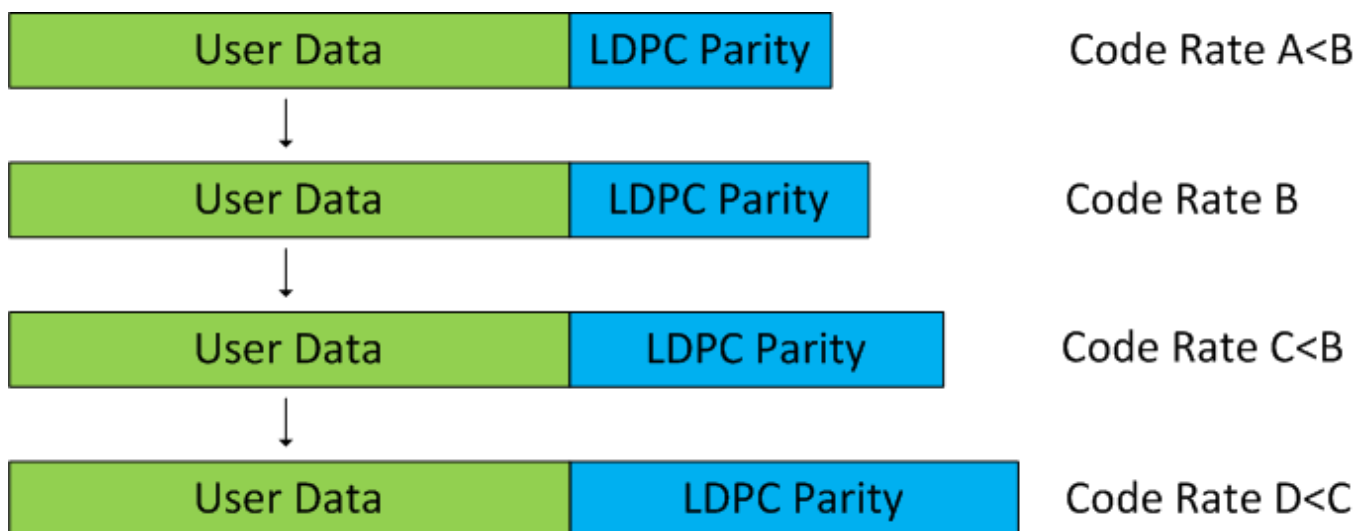
Remove some parity before writing to flash to increase code rate.

# Shortening



Leave parity fixed while decreasing data size to reduce code rate.

# Custom Code Rates

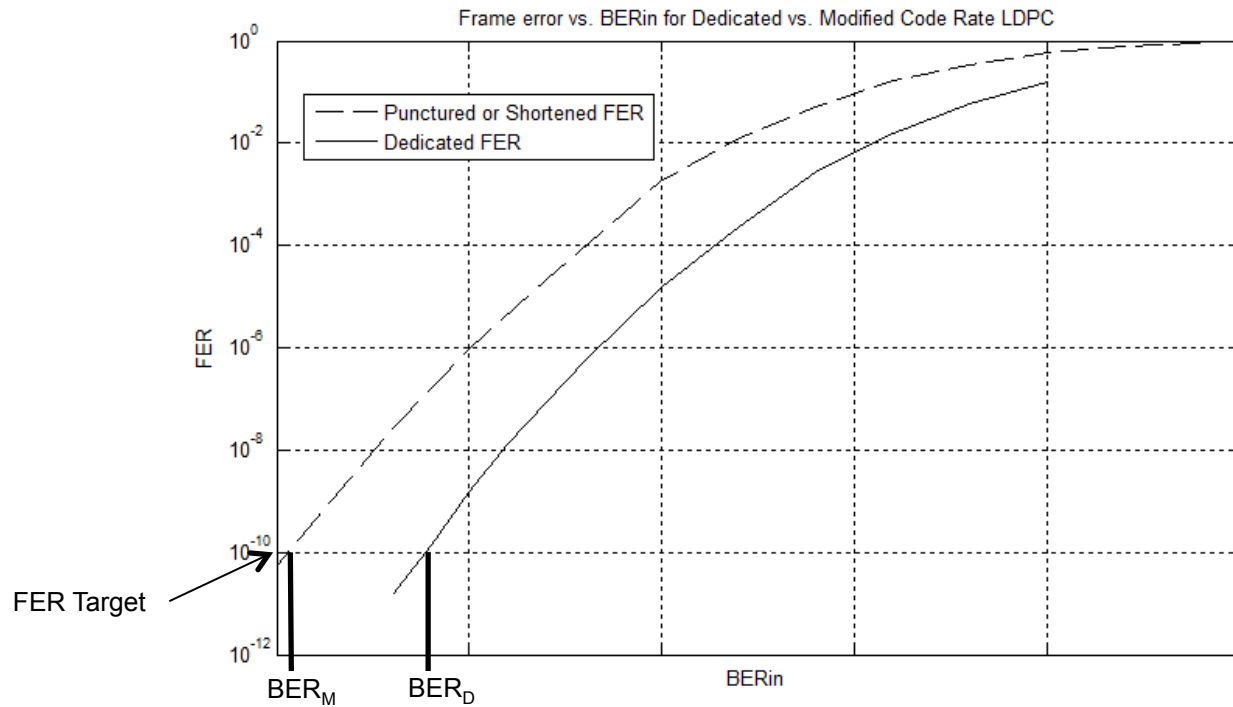


Leave data size alone and vary the amount of LDPC parity to select code rate.





# Performance Comparison (ECC)

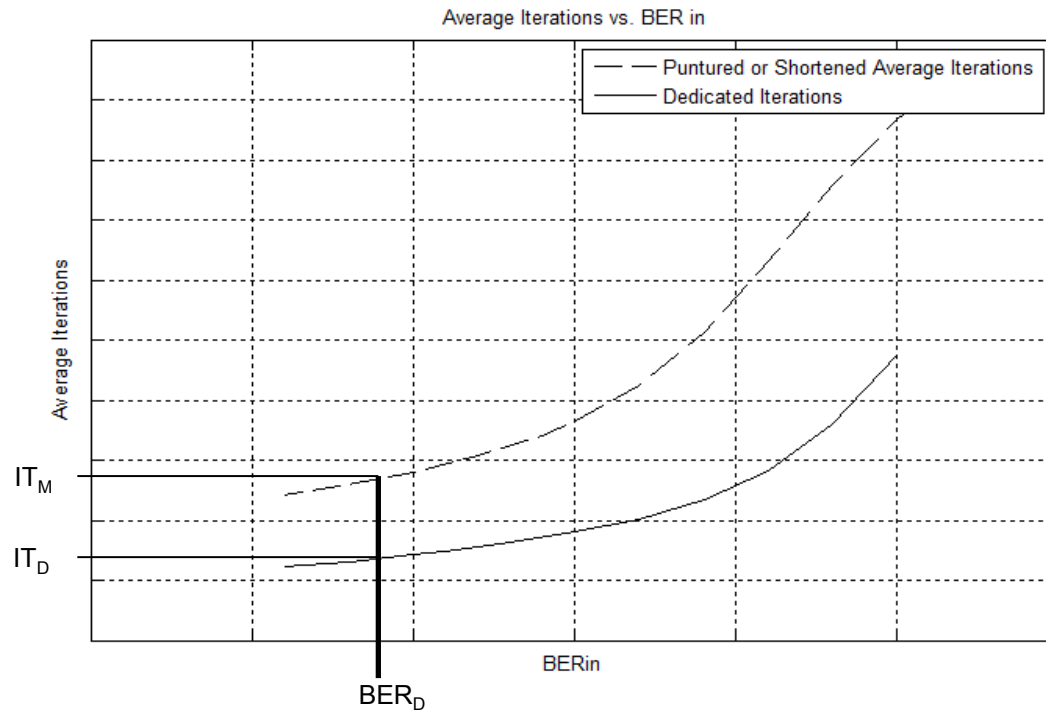


Define  
Relative Correction  
Performance

$$RCP = BER_D / BER_M$$



# Performance Comparison (Iterations)



Define  
Relative Iteration  
Performance

$$RIP = IT_D / IT_M$$

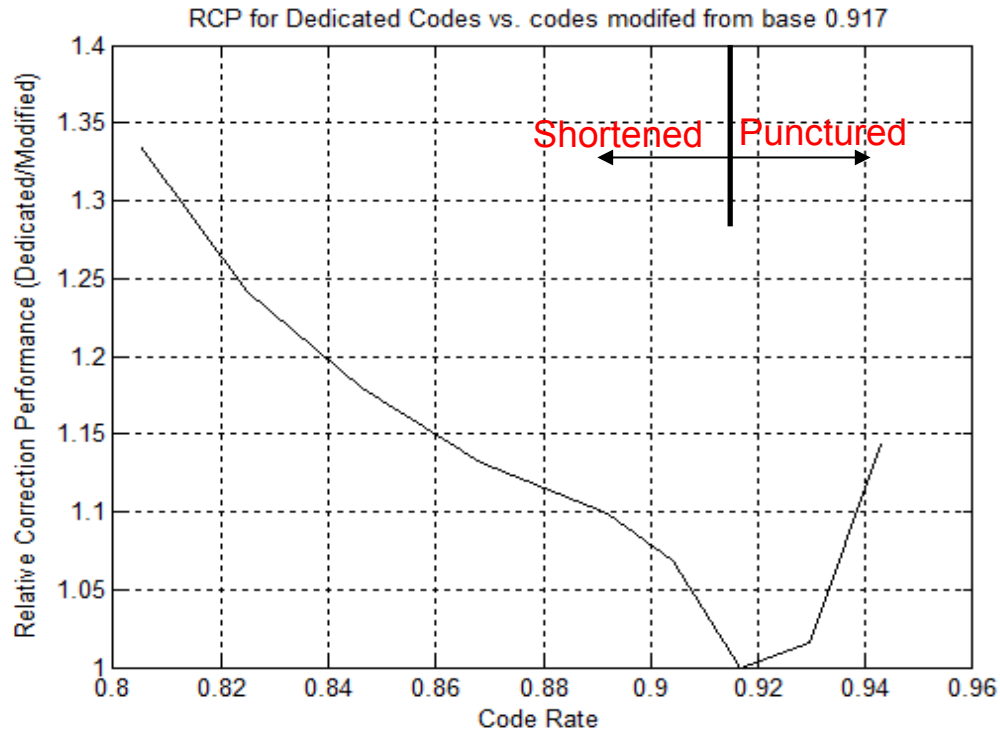


# Outline of Experiment

- Dedicated Codes
  - Design several custom codes between  $CR=0.8$  and  $0.95$
- Modified Codes
  - Start with native code at  $CR=0.917$
  - Match CR to dedicated codes
  - Use shortening to decrease CR and puncturing to increase CR
  - Compare RCP and RIP



# FER Results

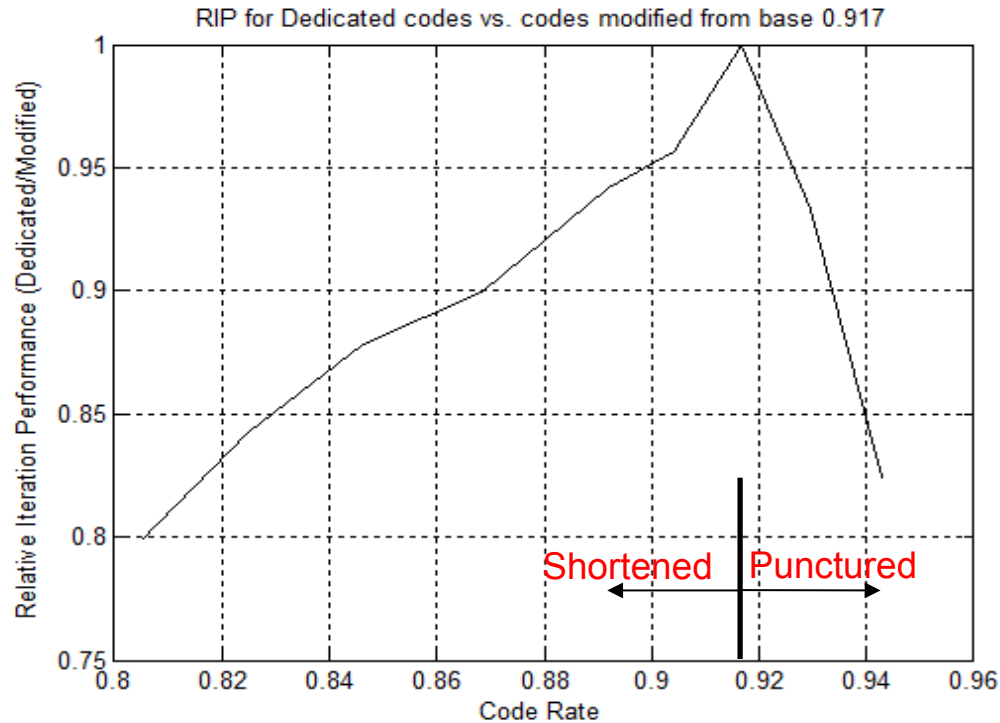


Dedicated codes improve error correction performance by up to 30% compared to Modified codes.

Small Modifications to CR of  $\pm 0.01$  do not significantly alter Error Correction Performance.



# Average Iteration Results



Dedicated codes have up to 20% reduction in Average Iterations compared to modified codes.

Small Changes to CR of  $\pm 0.01$  do not significantly alter Average Iterations.



## Summary

- NAND Flash Devices require flexible code rate selection
- The further a code is moved from its native state the worse the error correction performance and the higher the power consumption
- Dedicated codes exhibit up to 30% better error correction performance and 20% better iteration performance compared to punctured or shortened codes.



Thank You!

- Questions